Analog Power

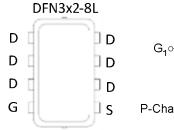
P-Channel 20-V (D-S) MOSFET

These miniature surface mount MOSFETs utilize a high cell density trench process to provide low $r_{DS(on)}$ and to ensure minimal power loss and heat dissipation. Typical applications are DC-DC converters and power management in portable and battery-powered products such as computers, printers, PCMCIA cards, cellular and cordless telephones.

- Low r_{DS(on)} provides higher efficiency and extends battery life
- Low thermal impedance copper leadframe DFN3x2-8L saves board space
- Fast switching speed
- High performance trench technology



PRODUCT SUMMARY				
V _{DS} (V)	r _{DS(on)} (OHM)	I _D (A)		
	$0.024 @ V_{GS} = -4.5V$	-8.4		
-20	$0.031 @ V_{GS} = -2.5V$	-7.4		
	$0.041 @ V_{GS} = -1.8V$	-6.4		



P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T _A = 25 °C UNLESS OTHERWISE NOTED)						
Parameter		Symbol	Maximum	Units		
Drain-Source Voltage		V _{DS}	-20	V		
Gate-Source Voltage			±8	v		
Continuous Drain Current ^a	T _A =25°C	ID	-8.4			
Continuous Drain Current	$T_{A}=25^{\circ}C$ $T_{A}=70^{\circ}C$	ID	-6.9	А		
Pulsed Drain Current ^b			-60			
Continuous Source Current (Diode Conduction) ^a		Is	±2.5	А		
	T _A =25°C	D_	2.5			
Power Dissipation ^a	$T_{A}=25^{\circ}C$ $T_{A}=70^{\circ}C$	гD	1.6	W		
Operating Junction and Storage Temperature Range		T _J , T _{stg}	-55 to 150	°C		

THERMAL RESISTANCE RATINGS						
Parameter	Symbol	Maximum	Units			
Maximum lunation to Amhiant ^a	t <= 5 sec	D	50	°C/W		
Maximum Junction-to-Ambient ^a	Steady-State	R _{THJA}	90	C/W		

Notes

a. Surface Mounted on 1" x 1" FR4 Board.

b. Pulse width limited by maximum junction temperature

Parameter	Symbol Test Conditions		Limits			I Init	
Farameter	Symbol	Symbol Test Conditions			Max	Unit	
Static							
Gate-Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = -250 \text{ uA}$	-0.3				
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 V, V_{GS} = +/-8 V$			±10	μA	
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = -16 \text{ V}, V_{GS} = 0 \text{ V}$			-1	μA	
Zero Gate Voltage Drain Current	DSS	$V_{DS} = -16 \text{ V}, V_{GS} = 0 \text{ V}, T_J = 55^{\circ}\text{C}$			-10		
On-State Drain Current ^A	I _{D(on)}	$V_{DS} = -5 \text{ V}, V_{GS} = -4.5 \text{ V}$	-60			Α	
		$V_{GS} = -4.5 \text{ V}, I_D = -8.4 \text{ A}$			0.024		
Drain-Source On-Resistance ^A	r _{DS(on)}	$V_{GS} = -2.5 \text{ V}, I_D = -7.4 \text{ A}$			0.031	Ω	
		$V_{GS} = -1.8 \text{ V}, I_D = -6.4 \text{ A}$			0.041		
Forward Tranconductance ^A	g_{fs}	$V_{DS} = -5 \text{ V}, I_{D} = -8.4 \text{ A}$		45		S	
Diode Forward Voltage	V _{SD}	$I_{s} = -1 A, V_{GS} = 0 V$		-0.5		V	
Dynamic ^b							
Total Gate Charge	Qg	$V_{DS} = -5 \text{ V}, V_{GS} = -4.5 \text{ V},$		19			
Gate-Source Charge	Q _{gs}	$V_{DS} = -5 V, V_{GS} = -4.5 V,$ $I_{D} = -8.4 A$		5		nC	
Gate-Drain Charge	Q _{gd}	$I_{\rm D} = -0.4$ A		5			
Turn-On Delay Time	t _{d(on)}			240			
Rise Time	t _r	$V_{DD} = -5 V, R_L = 5 OHM,$		580		nc	
Turn-Off Delay Time	t _{d(off)}	$V_{GEN} = -4.5 \text{ V}, R_G = 6 \text{ OHM}$		7		ns	
Fall-Time	t _f			4			

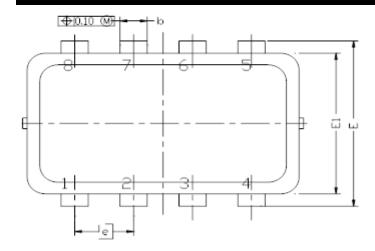
Notes

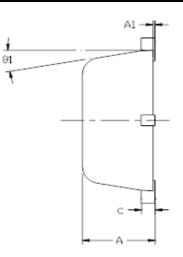
- a. Pulse test: $PW \le 300$ us duty cycle $\le 2\%$.
- b. Guaranteed by design, not subject to production testing.

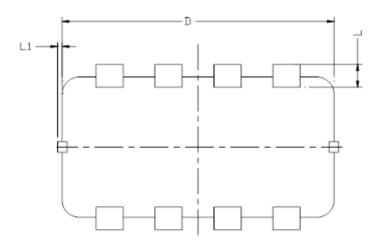
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DIM.	MILLIMETERS			INCHES			
DTM.	MIN	NDM	MAX	MIN	NDM	MAX	
Α	0.700	0.80	0.900	0.0276	0.0315	0.0354	
A1	0.00		0.05	0.000		0.002	
b	0.24	0.30	0.35	0.009	0.012	0.014	
С	0.08	0.152	0.25	0.003	0.006	0.010	
D	3.00 BSC			0.118 BSC			
E	6	2.00 BSC			0.079 BSC		
E1	1.70 BSC			0.067 BSC			
e	0	0.65 BSC			0.026 BSC		
L	0.20	0,275	0,400	0.008	0.011	0.0157	
L1	0		0.100	0		0.004	
θ1	0°	10°	12°	0°	10°	12°	

Note:

- 1. All Dimension Are In mm.
- 2. Package Body Sizes Exclude Mold Flash, Protrusion Or Gate Burrs. Mold Flash, Protrusion Or Gate Burrs Shall Not Exceed 0.10 mm Per Side.
- 3. Package Body Sizes Determined At The Outermost Extremes Of The Plastic Body Exclusive Of Mold Flash, Tie Bar Burrs, Gate Burrs And Interlead Flash, But Including Any Mismatch Between The Top And Bottom Of The Plastic Body.
- 4. The Package Top May Be Smaller Than The Package Bottom.

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